Contribution ID: **13** Type: **not specified**

TLM method for active doping profile evaluation

Monday 20 November 2017 13:50 (20 minutes)

Phosphorus and Boron doped profiles of silcion wafers have been investigated to reconstruct active doping profile from Transmission line measurements. It is known that total doping profiles is accessible through Secondary Ion Mass spectrometry analysis. Here this methods enable us to determine electrical active doping profiles and see the change of this concentration after irradiation . Un-irradiaded and irradiated samples have been analysed and preliminary results will be presented.

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Session Classification: Defects and material characterisation